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# SILICON NPN

BSV64

## PLANAR TRANSISTOR

**FEATURES** 

- V<sub>CBO</sub> = 100V
- V<sub>CEO</sub> = 60V
- I<sub>C</sub> = 2A

#### DESCRIPTION

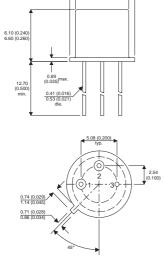
General Purpose NPN Transistor in a Hermetic TO39 Package

### **ABSOLUTE MAXIMUM RATINGS** (T<sub>case</sub> = 25°C unless otherwise stated)

V <sub>CBO</sub>	Collector – Base Voltage (open emitter)	100V	
V <sub>CER</sub>	Collector – Emitter Voltage ( $R_{BE} \leq 50\Omega$ )	80V	
V <sub>CEO</sub>	Collector – Emitter Voltage (open base)	60V	
V <sub>EBO</sub>	Emitter – Base Voltage (open collector)	5V	
I <sub>C</sub>	Collector Current (d.c.)	2A	
I <sub>CM</sub>	Collector Current (peak value)	5A	
I <sub>B</sub>	Base Current (d.c.)	1A	
P <sub>TOT</sub>	Total Device Dissipation @ T <sub>amb</sub> = 25°C	0.87W	
P <sub>TOT</sub>	Total Device Dissipation @ T <sub>Case</sub> = 50°C	5W	
T <sub>stg,</sub>	Storage Temperature	–65 to 200°C	
T <sub>i</sub>	Junction Temperature	175°C	
, Rθ <sub>j-c</sub>	Thermal Resistance Junction to Case	25°C / W	
Rθ <sub>j-a</sub>	Thermal Resistance Junction to Ambient	172°C / W	



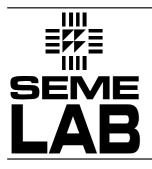
Dimensions in mm (inches)



8.51 (0.34 7.75 (0.305)

**Underside View** TO39 PACKAGE (TO-205AD)

Pin 3 = Collector



### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
V <sub>CEsat</sub>	Collector – Emitter Saturation Voltage	I <sub>C</sub> = 5A	I <sub>B</sub> = 0.5A			1	V
V <sub>BEsat</sub>	Emitter – Base Saturation Voltage	I <sub>C</sub> = 5A	I <sub>B</sub> = 0.5A			1.8	v
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 60V$	I <sub>E</sub> = 0			10	μA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V$	$I_{\rm C} = 0$			10	μΛ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 2V$	I <sub>C</sub> = 5A	25			
C <sub>C</sub>	Collector Capacitance at f = 1MHz	$I_{\rm E} = I_{\rm e} = 0$	V <sub>CB</sub> =10V			80	pF
f <sub>T</sub>	Transition Frequency at f = 20MHz	I <sub>C</sub> = 0.5A	V <sub>CE</sub> =5V	70	100		MHz
ton	Turn on Time	$I_{Con} = 5A; I_{Bon} = -I_{Boff} = 0.5A$				0.6	
toff	Turn off time	-V <sub>BEoff</sub> = 2V				1.2	μs

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